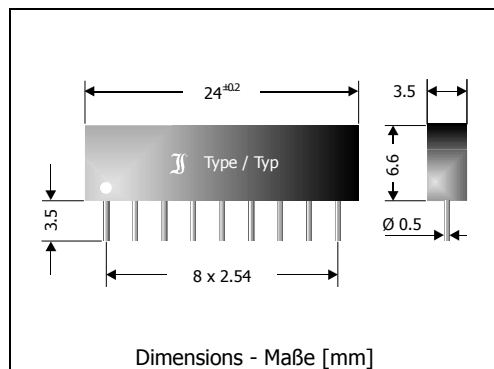


**DAN803 / DAP803 / DA4148A/K (200 mW)**
**Small Signal Diode Arrays**  
**Diodensätze mit Allzweckdioden**

Version 2008-06-06



Nominal power dissipation  
Nenn-Verlustleistung

200 mW

Repetitive peak reverse voltage  
Periodische Spitzensperrspannung

80 V

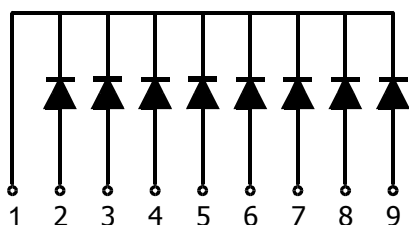
9-pin Plastic case  
9-Pin Kunststoffgehäuse

24 x 3.5 x 6.6 [mm]

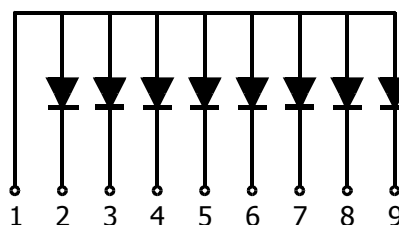
Weight approx. – Gewicht ca.

0.6 g

Standard packaging bulk  
Standard Lieferform lose im Karton



"DAN" / DA4148"K" common cathodes / gemeinsame Kathoden



"DAP" / DA4148"A" common anodes / gemeinsame Anoden

**Maximum ratings****Grenzwerte**

| Type<br>Typ      | Repetitive peak reverse voltage<br>Periodische Spitzensperrspannung<br>$V_{RRM}$ [V] <sup>1)</sup> | Surge peak reverse voltage<br>Stoßspitzensperrspannung<br>$V_{RSM}$ [V] <sup>1)</sup> |
|------------------|----------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| DAN803 = DA4148K | 80                                                                                                 | 80                                                                                    |
| DAP803 = DA4148A | 80                                                                                                 | 80                                                                                    |

|                                                                                                                      |                          |                        |                                             |
|----------------------------------------------------------------------------------------------------------------------|--------------------------|------------------------|---------------------------------------------|
| Max. average forward rectified current, R-load<br>for one diode operation only<br>for simultaneous operation         | $T_A = 25^\circ\text{C}$ | $I_{FAV}$<br>$I_{FAV}$ | 100 mA <sup>2)</sup><br>25 mA <sup>2)</sup> |
| Dauergrenzstrom in Einwegschaltung mit R-Last<br>für eine einzelne Diode<br>bei gleichzeitigem Betrieb beider Dioden | $T_A = 25^\circ\text{C}$ | $I_{FAV}$<br>$I_{FAV}$ | 100 mA <sup>2)</sup><br>25 mA <sup>2)</sup> |
| Peak forward surge current, 50 Hz half sine-wave<br>Stoßstrom für eine 50 Hz Sinus-Halbwellen                        | $T_A = 25^\circ\text{C}$ | $I_{FSM}$              | 500 mA                                      |
| Junction temperature – Sperrschichttemperatur<br>Storage temperature – Lagerungstemperatur                           |                          | $T_j$<br>$T_s$         | -50...+150°C<br>-50...+150°C                |

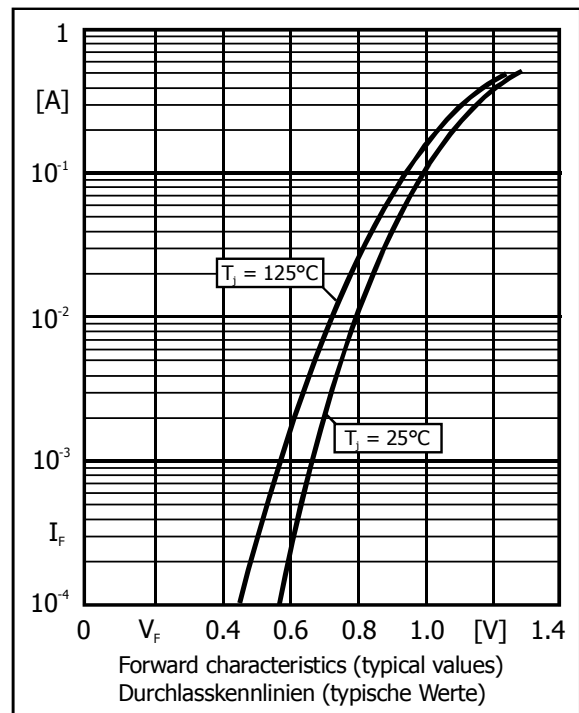
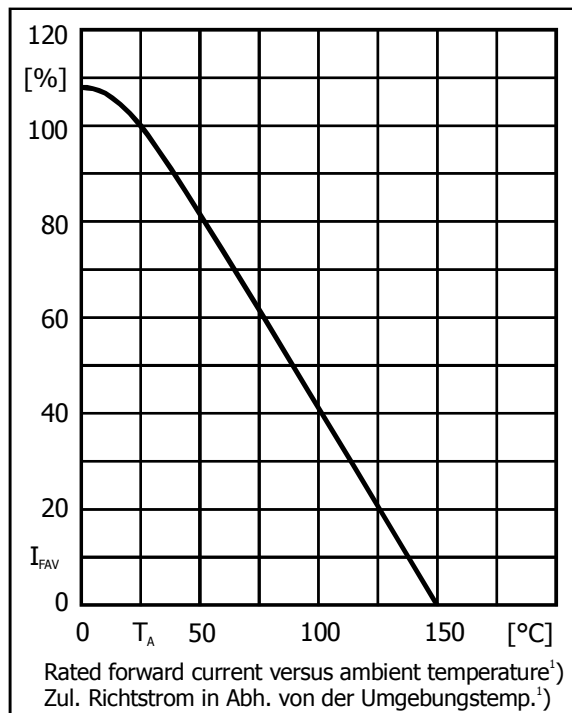
1 Per diode – Pro Diode

2 Valid, if leads are kept at ambient temperature at a distance of 3 mm from case  
Gültig, wenn die Anschlussdrähte in 3 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

# Characteristics

# Kennwerte

|                                                                               |                                                                                  |           |                      |
|-------------------------------------------------------------------------------|----------------------------------------------------------------------------------|-----------|----------------------|
| Forward voltage<br>Durchlass-Spannung                                         | $T_j = 25^{\circ}\text{C}$ $I_F = 10\text{ mA}$                                  | $V_F$     | $< 1.0\text{ V}^1)$  |
| Leakage current<br>Sperrstrom                                                 | $T_j = 25^{\circ}\text{C}$ $V_R = 20\text{ V}$                                   | $I_R$     | $< 25\text{ nA}$     |
| Reverse recovery time<br>Sperrverzug                                          | $I_F = 10\text{ mA}$ through/über<br>$I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}$ | $t_{rr}$  | $< 4\text{ ns}$      |
| Thermal resistance junction to case<br>Wärmewiderstand Sperrschicht – Gehäuse |                                                                                  | $R_{thC}$ | $< 85\text{ K/W}^2)$ |



1 Per diode – Pro Diode

2 Valid, if leads are kept at ambient temperature at a distance of 3 mm from case  
Gültig, wenn die Anschlussdrähte in 3 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden